



Status of operation of the CMS GEM system

3rd DRD1 Collaboration Meeting 9-13 December 2024 CERN, 2024-12-09

Simone Calzaferri

University of Pavia (Italy)

On behalf of the CMS Muon Group

Table of contents

- 1. Detectors' efficiency
- 2. Timing and trigger performance
- 3. HV stability
- 4. Production of detectors

GEM detectors installed in CMS in 2024



GEM: Gas Electron Multiplier

- Triple-GEM detectors in CMS
- Gas mixture:
 - Datataking: Ar/CO_2 (70/30)
 - Year End Technical Stop: pure CO₂

• GE1/1:

- η coverage: 1.55 < | η | < 2.18
- 144 detectors installed
- Angular coverage: 10° with two chambers stacked
- Timeline:
 - Installed in LS2, operated from the bennining of Run-3
 - Lessons learned after 3 years

GE2/1:

- η coverage: 1.62 < | η | < 2.43
- 3 chambers installed, 12 modules installed in total (entire GE2/1 system: 288 modules)
 - Angular coverage: 20° with two chamber stacked
- Timeline
 - **Demonstrator:** operated from the beginning of Run 3 (3 years)
 - Chambers in negative endcap: installed in YETS23/24

GE1/1 vs GE2/1



Back chamber M4 M3 M2 M1



GE11

- 2 kind of modules
- GEM foils: all manufactured with single mask etching

GE21

- 1 chamber is made of 4 modules
- 8 kind of modules
- GEM foils: some manufactured with single mask etching, some with double mask

9/12/2024

Goal of GE1/1 and GE2/1

- Increase the muon spectrometer redundancy to
 - Sustain high radiation flux
 - Keep under control the trigger rate in the endcap region



- The addition of GEM can help in improving the evaluation of the muon transverse momentum
 - How: exploit the increase of the lever arm available for muon local bending between GEM and CSC
 - GE1/1 pairs with the CSC chambers ME1/1
 - GE2/1 pairs with the CSC chambers ME2/1

GE1/1

~18cm

19

~44cm

ME1/1

Even

Odd

Integration of GEM in Level-1 Trigger



- Activated the correction of the slope of the local muon bending between CSC and GEM
 - GEM offer additional hits which can be combined with CSC
 - Combination of the CSC Local Charged Track
 (LCT) with GEM hits
 - The improved LCT is sent to the Endcap Muon Track Finder (EMFT)
- Deployed in CMS on 30th September 2024
 - Collected around 12 fb^{-1} of p-p collisions data after the deployment
 - No increase of trigger rate in the region covered by GE1/1



DISCHARGES

Impact: HV instability, short circuits in GEM foils, reset and dead channels in electronics



SHORT CIRCUITS IN GEM FOILS Impact:

Inefficient areas, lower voltage applied to the whole foil

Issues summary



VTRx instability Impact: Areas of electronics (part or full detectors) not read



PCB bending

Impact:

Local difference in electric fields (and so lower efficiency). Degradation of hit time of arrival (and so time resolution)



Non passivation of PCBs copper Impact: Oxidation signs



Copper dust on GE2/1 PCBs Impact: Generation of short circuits

Detectors' efficiency

Electronics



- Front-end electronics: VFAT3 chips
 - GE1/1: 24 per detector
 - GE2/1: 12 per detector
- Groups of VFAT3 chips read by GBT (Giga Bit Transceivers)
- OptoHybrid board on the detector hosting GBTs and FPGA
 - FPGA: Virtex 6
- Data sent by the OH to the backend electronics by VTRx optical transceivers





Efficiency after HV scan 2024



• HV working point optimized

- Tuned chamber by chamber to maximize the detector efficiency and minimize its discharge rate
- Tested several electronics configurations for the VFAT front-end chip
 - Adopted:
 - VFAT chip pre-amplifier in High gain
 - VFAT Constant Fraction Discriminator (CFD) enabled

• Efficiency:

- Before HV scan 2024: 87%
- Now: 94.7 %

• Automation:

 Produces efficiency results for each LHC fill in few days (limited by transfer time of data to Tier-0)

Detectors' efficiency in detail



GE2/1 efficiency

Chamber: GE21-M-16-L1 **Status:** not contaminated by copper dust



Timing and trigger performance

Timing: GE1/1 detectors

- Affected by: mechanical bending of the PCBs
- What happens:
 - A. The time of arrival of one hit depends on its position in the chamber
 - B. The time resolution per strip is degraded proportionally to the time of arrival

• Effect:

- Modulation per eta partition on the time of arrival, resulting in degradation of time resolution in general
- Valley: edge of the chamber
- Peaks: center of the chamber (the PCB is distant to planar scenario)
 - On the wide side of the chamber the bending effect is more important
 - This effect is more important on long GE1/1 detectors
- GE1/1 can reach ME0 time resolution (10 ns) where the detector is flat ([12], page 94)



Ideal case



PCB bending



Timing of GE1/1: delayed signal



 Improvement of effect A (time resolution function of position in the chamber)

• Implemeted by:

 Slowing the delayed hits to the slower ones, applying to a group of strips a delay with Bunch Crossing (BX) granularity

• Result:

• Average arrival time within 1 BX

Timing in GE1/1: improved cluster timing





 Improvement of effect B (time resolution function of hit time of arrival)

• Fact:

- To properly identify the muon time of arrival you need to **catch the center of the cluster** of strips firing
- Time resolution per strip is affected by cross-talk bipolar induced signals on neighbouring strips (early firing)

• Improved by:

- Using Constant Fraction Discriminator (CFD) of VFAT3
- Removed cross talk signal of the strips at the edge of the cluster in firmware

^{9/12/2024}

Time resolution: global improvement



Improvement of mode value

- Old firmware: 15.3 ns
- New firmware: 12.3 ns

• Cost:

- Increased Level 1 Trigger (L1T) latency in input to the Endcap Muon Track Finder (EMTF)
- 2 BX for the CFD
- 1 BX for the cross talk cancellation

HV stability

HV: How we power the detector



Power full GEM stack: 7 electrodes needed

Configuration $\mathbf{I_{eq}}=690~\mu\mathbf{A}$ (Gain ≈ 10^4)					
Drift	776 V	G1Top	387 V		
G1Bot	302 V	G2Top	379 V		
G2Bot	604 V	G3Top	362 V		
G3Bot	431 V				

• Proportions among stack voltages

Fixed by a reference resistive divider used in quality control in laboratory \rightarrow the current flowing in the divider identifies a set of voltages (I_{eq})

 Multichannel power supply boards used in CMS (A1515BTG)

Discharges

- What is a discharge: transient transfer of charge between detector planes
- When: mainly during LHC pp collisions
 - HV working point in 2024: 680-705 μA
 - Tuned chamber by chamber to maximize the detector efficiency and minimize its discharge rate
 - 2024 p-p collisions
 - Instantaneous Luminosity: $O(10^{34}) cm^{-2}s^{-1}$
 - Average rate of discharges: < 3 discharges per detector per hour
 - 2023 Pb-Pb collisions
 - Instantaneous Luminosity: $O(10^{27}) cm^{-2}s^{-1}$
 - Average rate of discharges by the whole system (143 GE1/1 detectors): 5 discharges per LHC fill
- Impact:
 - Can create damages to the foils (short circuits)

Shorts at 2024-11-25	HV sectors	Foil	Detectors
GE11_M	28	23	20
GE11_P	27	24	20
GE11 total	55	47	40
GE21_M	4	4	3
GE21_P (M4 disconnected)	6	3	2

- Can create resets or damages to the electronics: currents find the least resistance path through the
 electronics
 - Channels:
 - Active: GE1/1: 93 %, GE2/1: 100 % (all VFATs communicate)
 - Damaged: 0.3%, Noisy & permanently masked: 1.5%

Impact of a short circuit

- 1. Zero efficiency in the HV sector affected by the short circuit
 - GE1/1: 2.5 % of area per HV sector in a short detector, 2.1 % for a long detector
 - 40 (47) HV sectors per GEM foil in GE1/1 short (long) detectors
- 2. Drop of the voltage effectively applied to the foil
 - The voltage drops on the HV filter resistors, globally lowering the whole foil, around 6% in GE1/1
 - This second effect starts to become relevant if more than one short is present in the same chamber.
 - Evaluations are ongoing thanks to special runs taken in 2024



Evolution of short circuits in Run-3



Mainly affected foil: GEM 3

 Closest to the readout and crossed by the highest charge during avalanche multiplication of primary ionisation electrons

Conditions of short circuits generation:

 Mostly due to discharges, voltage ramp up and magnet ramps

Conditions of short circuits healing:

 Mostly due to discharges, voltage ramp, magnet ramp, slow consumption of the short circuit

YETS24/25

 Keep minimal HV on GE1/1 during the whole YETS (300 V on the foils, gaps OFF), to mimize the stress at the repower and the contribution of diffusion of oxides in the generation of short circuits

Short circuits: Magnet operations

- During a magnet ramp:
 - Short circuits mostly generate in the low field region

(very beginning of a magnet ramp up or at the very end of a magnet ramp down)

- Implemented HV protection for magnet operations
 - HV on GEM foils set to 420 V, gas gaps turned OFF
 - Article on tests done with Goliath Magnet in CERN North Area in 2021 <u>10.1088/1748-0221/18/11/P11029</u>



Events in the plot: magnet ramp ongoing and HV ON

Detectors' production

Production of PCBs

- In summer 2023 it was discovered an issue in the production of PCBs
 - GE1/1 PCBs were not passivated
 - GE2/1 PCBs were not passivated and sand blasted → copper dust in the detectors



More details: <u>RD51 collaboration meeting</u> (7 December 2023) [10]

Investigations and actions

Ageing detector



GE11-X-SHORT-0002

GE1/1 extracted from CMS



Green stains



Brown stains

- Signs of oxidation in irradiated area in the GE1/1 ageing detector
 - White and blue stains
- Exctracted and replaced 4 GE1/1 detectors from CMS
 - Found **signs of oxidation** in 2 of the 3 inspected detectors (green and brown stains)
- Actions:
 - Started cleaning both of GE2/1 GEM foils stack and of PCBs
 - How: chromic acid bath
 - Tests in magnet MNP22 in North Area
 - Extraction from CMS in January 2025
 - 6 detectors (3 GE1/1 Super-Chambers)
 - Why: investigation on oxidation

Conclusion

Summary on 2024 operations

- Operations team tried to squeeze all the efficiency obtainable so far
 - HV compensation of short circuits: needed improvements in the Detector Control System (DCS)
- Time resolution: 12.3 ns
- GEM included in L1 Trigger
 - Next step of integration in the hands of Endcap trigger group
 - GEM team will continue to assist the integration from the detector side

• Investigations on detectors ongoing

- Cleaning of GE2/1 detectors
- Role of oxidation
- Digging further on role of magnetic field ramps in generation of discharges and short circuits (performed 2 tests in magnetic field from 2021)
- Many more aspects investigated but not possible to cover in the talk time range
 - There are **references and material in backup** for the interested auditorium

References

- [1] CMS Collaboration, The history of GEM foil short circuit generation and healing (2021-2023), CMS-DP-2024-050, https://cds.cern.ch/record/2904363.
- [2] CMS Collaboration, GE1/1 discharges plots, CMS-DP-2023-091, <u>https://cds.cern.ch/record/2883614</u>.
- [3] EP-ESE Electronics Seminars, The Curious Case of VTRx Receiver Failures, <u>https://indico.cern.ch/event/1099169</u>
- [4] CMS Collaboration, GE1/1 electronics performance, CMS-DP-2024-120, https://cds.cern.ch/record/2917572
- [5] CMS Collaboration, Study of correlation between baseline current and Hit Rate in GE1/1 chambers at the CMS Experiment, CMS-DP-2024-117, <u>https://cds.cern.ch/record/2916757</u>
- [6] G. Mocellin, Performance of the GE1/1 detectors for the upgrade of the CMS muon forward system, CERN-THESIS-2021-327
- [7] CMS Collaboration, Performance and quality control of the first CMS GE2/1 muon production chambers, CMS-DP-2024-075, <u>https://cds.cern.ch/record/2908777</u>
- [8] CMS Collaboration, Measurements of pT Dependent Bending Angles in the CMS GE1/1-ME1/1 System, CMS-DP-2024-047, <u>https://cds.cern.ch/record/2904360</u>
- [9] CMS Collaboration, GEM performance results with 2024 data, CMS-DP-2024-073, https://cds.cern.ch/record/2908775
- [10]A. Pellecchia, Status of CMS GEM Production, RD51 Collaboration Meeting, 7 December 2023 <u>https://indico.cern.ch/event/1327482/contributions/5686633/attachments/2767175/4820306/CMS%20GEM%20productions/20status%20-%20RD51%20Dec%202023%20(5).pdf</u>
- [11] M. Abbas et al., Impact of magnetic field on the stability of the CMS GE1/1 GEM detector operation, 2023 JINST 18 P11029, DOI: <u>10.1088/1748-0221/18/11/P11029</u>
- [12] F.Nenna, Performance in a high-rate environment of triple-GEM detectors for the Phase-2 upgrade of the CMS detector, CERN-THESIS-2024-114, <u>https://cds.cern.ch/record/2906703</u>



Backup for HV

The HV working point



- How to fix the voltages on the single channel: these numbers are determined by a reference resistive divider used for the quality control of the detectors
- How to have flexibility: in CMS (P5) a multichannel power supply board (A1515BTG) is used, applying the voltage settings aforementioned and allowing to modify each of the 7 channels
 - This voltage configuration is equivalent to that obtained by a given current flowing the referece resistive divider. So a voltage setting (I_{eq}) is identified by this current

Configuration $\mathbf{I_{eq}}=690~\mu\mathbf{A}$ (Gain $pprox 10^4$)					
Drift	776 V	G1Top	387 V		
G1Bot	302 V	G2Top	379 V		
G2Bot	604 V	G3Top	362 V		
G3Bot	431 V				

HV patch panel

A1515-TG board



Voltage settings

Equivalent divider current Ieq [µA]	580	690	700	710
Voltage on drift gap [V]	653	776	788	799
Voltage on GEM1 foil [V]	325	387	392	398
Voltage on transfer 1 gap [V]	254	302	307	311
Voltage on GEM2 foil [V]	319	379	385	391
Voltage on transfer 2 gap [V]	508	604	613	621
Voltage on GEM3 foil [V]	305	362	368	373
Voltage on induction gap [V]	363	431	438	444
Electric field in drift gap [kV/cm]	2.18	2.59	2.63	2.66
Electric field in GEM1 foil [kV/cm]	65.0	77.4	78.4	79.6
Electric field in transfer 1 gap [kV/cm]	2.54	3.02	3.07	3.11
Electric field in GEM2 foil [kV/cm]	63.8	75.8	77.0	78.2
Electric field in transfer 2 gap [kV/cm]	2.54	3.02	3.07	3.11
Electric field in GEM3 foil [kV/cm]	61.0	72.4	73.6	74.6
Electric field in induction gap [kV/cm]	3.63	4.31	4.38	4.44
Total gain	$(3.99 \pm 0.14) \cdot 10^2$	$(1.98 \pm 0.08) \cdot 10^4$	$(2.83 \pm 0.11) \cdot 10^4$	$(4.05 \pm 0.17) \cdot 10^4$





• What is a discharge?

- Transient transfer of charge between the detector planes
- How it looks like?
 - Spike in current above the baseline current
- Impact?
 - It can trigger HV trips → the current spike can overcome the current limit of the HV channel
 - It can damage channels of the front-end electronics, if the discharge propagates towards the readout plane

CMS Preliminary



CMS Preliminary


CMS Preliminary



2023 (13.6 TeV)





Discharge rate during Pb-Pb collisions

- Low discharge rate during Pb-Pb collisions
- Much lower instantanous luminosity from the LHC
 - p-p collisions: $\sim 10^{34} cm^{-2} s^{-1}$
 - Pb-Pb collisions: $\sim 10^{27} cm^{-2} s^{-1}$

Quantity	Average per fill	Total
Discharges (143 detectors)	5.9 ± 0.7	347
Delivered luminosity	$34.0 \pm 2.7 \mu b^{-1}$	2005.7 μb ⁻¹

Baseline current in presence of beam



Baseline current vs LHC luminosity



Discharge rate Vs Luminosity



- Data of 5 LHC fills analysed
 - Fixed HV working point: $I_{eq} = 690 \ \mu A$
- Correlation between discharge rate vs luminosity of the LHC

• Complications:

- Conditioning effect: The discharge rate for a given chamber can change in time → generation or removal of imperfections in the GEM foil which generate the discharges
- Damages in the foils: if a short circuit is generated a lower effective voltage is applied to the foil

• To study:

• Dependence of the discharge rate on the HV working point

Background current vs Luminosity



• No sign of saturation in the hit rate

Homework

- Analyze more fills, in particular of HV scan 2024
- Study the dependence on the HV working point
- Study the role of short circuits

Background Current vs Luminosity



- Two-dimensional binned distribution of the timeweighted baseline current as a function of instantaneous luminosity.
- The current is weighted during the "lumi section" corresponding to the measurement of instantaneous luminosity, where a "lumi section" is a reference time interval used by CMS corresponding to ~ 23 seconds.
- This plot is relative to the chamber GE1/1-P-01-L1, paired in the HV with GE1/1-P-01-L2 (May 2023). This distribution refers to the current in the G3Top channel of A1515 board, powering the GEM3 foil. It is shown the corresponding working-point, the G3Bot voltage status and the linear correlation coefficient ρ , whose error is estimated by $\sqrt{\frac{1-\rho^2}{N-2}}$ where N is the number of all entries.
- The outliers in bottom left part of the plot are due to beam separation ("emittance") scans near the start of CMS data taking, which cause sudden variations in instantaneous luminosity and current.

Short circuits in GEM foils

Short circuit in a GEM foil?

Time



• What is:

Connection between top and bottom face of a GEM foil

• Why:

- Defects or depositions on GEM foil can create temporary or permanent short circuit between top and bottom electrode
- How does it look like?:



Time

10 MΩ

10 MΩ

GEM/Top

GEM Bottom

10 MΩ

~ 100 Cm2

10 MΩ

Design of HV distribution on the detector

GE1/1: used for all three GEM foils

 R_{f2}

230 kΩ

R_{f1}

100 kΩ

R_{f1}

100 kΩ

2.2 nF

 $C_f = 2.2 \text{ nF}$

HV

HV



- 40 (47) HV sectors in short (long) GE1/1 chambers
- HV sectors just on the top face of the GEM foil

• GE2/1

- HV sectors on both sides of the foil
- The number of sectors depends on the kind of GE2/1 module (19-46 HV sectors)
- 100 k Ω resistor applied on the bottom of foils GEM1 and GEM2
- No resistor applied on the bottom of foil GEM3, just the HV filter

GE2/1: used for foils GEM1 and GEM2

R_{f2}

230kΩ

Cf



Magnet ramp sign



Short circuits generated and healed per foil



Short circuits: gas mixture



Short circuits: gas vs HV



Short circuits: HV during magnet ramp



Short circuits: HV value



Mechanisms involved in generation/healing of shorts in GE1/1 GEM foils



Short circuits: operation period period



Operative context for short generation and healing





Conditions of generation:

 Mostly due to discharges, voltage ramp up and magnet ramps

Conditions of healing:

Mostly due to discharges, voltage ramp, magnet ramp, slow consumption of the short circuit

Short circuits: Status at 2024-11-25

Shorts at 2024-11-25	HV sectors	Foil	Detectors	
GE11_M	28	23	20	
GE11_P	27	24	20	
GE11 total	55	47	40	
GE21_M	4	4	3	
GE21_P (M4 disconnected)	6	3	2	
	Foils with at least one HV sector affected by short circuit	Detectors with at least one fo with at least one HV sector affected by short circuit		

Non conductive short circuits



Ignition consumption mechanism

Counts

Backup for Hardware in CMS

Investigation on GE1/1



- Exctracted and replaced 4 GE1/1 detectors from CMS
- Found signs of oxidation in 2 of the 3 inspected detectors
- Additional extraction maybe possible in YETS24/25



Back chamber Front chamber **M4 M8 M**3 **M7 M2 M6** M5 **M1** Layer 2 Layer 1 Installed off yoke

Farther from the interaction point

Installed on yoke Closer to the interaction point



HV distribution GE2/1



Cleaning of GE2/1

- Recleaning detectors and installed in CMS during YETS23/24
 - One detector never contaminated by dust
 - This detector now has one short circuit in one module
 - One detector with the PCBs recleaned from dust
 - This detector has three short circuits in total among the 4 modules
- Started cleaning also the GEM foils stack
 - How: chromic acid bath



How to validate the cleaning procedure before installing in CMS?

Magnet test 2024: Test of detectors in magnetic field (October-November 2024)

- Where: Magnet MNP22 in CERN North Area
- Detectors tested:
 - 2 GE2/1 recleaned
 - 1 GE2/1 never contaminated by dust
 - 1 GE2/1 still contaminated from dust
 - 2 GE1/1 detectors extracted from CMS and with oxidation signs
 - 2 ME0 modules
- All the detectors showed some instability and a decreasing number of discharges after several magnet ramp cycles
 - GE1/1 still unstable after several ramps (generation of short circuits) \rightarrow investigation ongoing
- The detailed analysis is now ongoing









Cooling manifold



Upgraded cooling manifold from 6 to 3 chambers per line

Backup for Efficiency

Detectors' efficiency in detail



Efficiency vs HV working point



Chamber efficiency



• HV scan 2024

- Investigated several HV working points
- Tested several electronics configurations
- New HV working point tuned per chamber
 - Depending on chamber efficiency vs HV curve: look if the chamber is at efficiency plateau at a given I_{eq}
 - Chamber discharge rate
- Efficiency now: 94 %
 - Set of working points used: $I_{eq} = 685 700 \ \mu A$

GE2/1 efficiency



- Efficiency map for a GE2/1 chamber installed in CMS, taken from a 2023 run corresponding to Lumi = 395 1/pb.
- This chamber was powered on at HV 695µA equivalent divider current and using the frontend chip (VFAT) preamplifier in medium gain and Constant Fraction Discriminator (CFD) comparator settings.
- The data is divided into VFAT readout regions (128 channels per chip). Plotted is the fraction of events where a reconstructed hit is found near a propagated track on each VFAT, and given in local coordinates.
- Muons used in the calculation : Standalone muons with at least 15 hits (at least 1 in ME2/1), $\chi^2 < 5$, pT > 10 GeV. Fiducial cuts on the detector : region of 1.5cm from the border of the eta partition and 0.0075rad from the lateral edges of the chamber.

Backup for Electronics
Electronics stability



- Channels:
 - Active: GE1/1: 93 %, GE2/1: 100 % (all VFATs communicate)
 - **Damaged:** 0.3%
 - Noisy & permanently masked: 1.5%

Electronics stability issues from:

- GBTx not fetching correct configuration from fuses after power-on
 - Fixed by: Interaction with DCS for automatic power cycle
- VTRx glue outgassing → GBT unstable → Lack of publication of FPGA temperature → Safety requirement: power off the electronics
 - Some VTRx are expected to bake in situ during operations
 - LS3: Installation of cooled VTRX on GE1/1
 - 4 GE1/1 detectors with cooled VTRX installed in CMS during YETS23/24: stable
- Front-end chips (VFAT) communication issues
 - Probable consequence of aforementioned issues
- Minimized by:
 - During run: progressive masking of the affected front-end
 - During interfill: electronics power cycle and reconfiguration
- Single Event Upset (SEU) → Lack of publication of FPGA temperature for a block of 12 chambers controlled by 1 backend card → Power off of electronics for all of them
 - Mitigated by reprogramming the FPGA in the bakground (during the run) \rightarrow no power off of the chambers

Electronics stability: VTRx cooling



Zoom view of Opto-Hybrid bottom side

Bottom view of the GE1/1 Opto-Hybrid with new VTRx cooling

Installation in YETS-23/24

- 2 super-chambers (4 detectors) in CMS equipped with cooled VTRx and RSSI (Receiver Signal Strenght Indicator) reading
- GE11_M_25 and GE11_M_26

• How

- Thermal pad (Blue strip)
- Copper plates
- Potential overall improvement in efficiency: ~6 %
 - Why: the electronics is more stable
 →More electronics in total can be read

Sigle Event Upset (SEU)



VFAT 3 chip



Backup for Timing and Trigger

Timing in GE1/1: improved FPGA firmware



- Distribution of the time resolution as a function of the trigger pad (pair of two readout strips) for a long GE1/1 chamber, with different firmware versions.
- Each entry represents the width of the time distribution of a group of 16 trigger pads (one quarter of a GE1/1 readout sector).
- The new on-chamber electronics (OptoHybrid) FPGA firmware has a feature that we call "x-talk suppression". It consists in cancelling the hits coming from the interreadout-strip x-talk, which are assigned an earlier Bunch Crossing (BX) with respect to the muon hit.
- The plot shows results from collision runs with both firmware versions. For all runs, the selected GEM hits are the ones matching to a muon track with $p_T > 10$ GeV.
- The time resolution is clearly improved for the new firmware:
- In the low in area of the detector (wide side), the time resolution worsens significantly, due to the bending of the PCBs in the GE1/1 chambers.

Timing in GE1/1: delays

- Content: Distribution of the average arrival time as a function of the trigger pad (pair of two readout strips) for a Long GE1/1 detector
 - Each point in the plot represents the width of the time distribution of a group of 16 trigger pads (one quarter of a GE1/1 readout sector).
- Kind of run: collision runs with both firmware versions.
- Cuts on muons: For all runs, the selected GEM hits are the ones matching to a muon track with pT > 10 GeV.
- Implementation of signal delays: this effect is partially mitigated by delaying earlier hits to later ones. Before we apply any corrections, the arrival times span 4 BXs (of 25 ns). These corrections with BX granularity are applied to groups of 16 strips. Therefore, after applying the corrections, all arrival times end up in the same BX. But the signals are delayed in general and so the latency of the system increased.





Time resolution



- Distribution of the time resolution of GE1/1, with different Firmware (FW) versions ; each entry represents the width of the time distribution of a group of 16 trigger pads (one quarter of a GE1/1 readout sector).
- Tests with new on-chamber electronics (OptoHybrid) FPGA firmware with the feature "x-talk suppression". It consists in cancelling the hits coming from the interreadout-strip x-talk, which are assigned an earlier Bunch Crossing (BX) with respect to the muon hit.
- The plot shows results from collision runs with standard firmware; results from collision runs obtained emulating the behavior of the new firmware; results from collision runs with an experimental version of the new firmware. For all runs, the selected GEM hits are the ones matching to a muon track with pT > 10 GeV.
- Results: the MPV value decreases from 15.3 ns with the standard firmware to 12.3 ns with both the emulator and experimental versions of the new FW.

GEM in Level 1 Trigger (L1T)

CSC (Cathode Strip Chambers) 6 layers

Possible usage (reduction):

- Enhance the single station pT estimation

- Increase the efficiency in case of missing CLCT (Cathode Local Charge Track)



GEM Super-Chamber 2 layers

Possible usage (redundancy):

- Replace missing CSC LCT
- Improve efficiency on the edge of the chambers
- Improve track parameters estimation

Hit occupancy plot



Higher eta \rightarrow higher number of hits due to background radiation

During a high multiplicity event a lot of fake hits are present on top of those due to the background (can be noticed from the scale). In particular the hits concentrate on the edges of VFAT chips, each reading a group of 128 strips

 $\times 10^3$

160

140

120

100

80

60

40

20

Z

GE2/1 residuals



- Distribution of hit residuals on a GE2/1 module in a GEM cosmic-ray stand, powered on at an equivalent divider current of 700µA.
- The distribution is fit to a Gaussian and the spatial resolution is taken to be the width of the Gaussian.
- The spatial resolution of this particular module and region is 1.60 mm, without alignment.
- The expected spatial resolution is under 300µm.
- The duration of the cosmic run was 69 hours and 46 minutes. This module is a part of the GE2/1 chamber currently installed in CMS (GE21-M-16L1).

Muon bending angle



- Implemented alignment between CSC (ME1/1) and GEM (GE1/1) chambers
 - Different distance between ME1/1 and GE1/1
 - Even chamber: 18 cm
 - Odd chamber: 44 cm
 - Bending angle distribution with Global muons (30 GeV < p_T^{GLB} < 35 GeV) $\phi_{bending} = \phi_{ME1/1 \, segment} - \phi_{GE1/1 \, rechit}$
 - p_T dependence of the bendind angle distribution ($\phi_{bending} \propto p_T^{-1}$)



High multiplicity events

- What: high multiplicity events in the GE1/1 chambers
- Why:
 - The L1 trigger signal for accepting an event (L1A) generates a noise signal that can overcome the threshold set in the VFAT3 for the acquisition of data, ~ 160 BX later
 - If a new L1A signal comes data in that time window, the noise signal is acquired
- Minimized by: multi-BX window masking applied at trigger level: 95% of events filtered
 - 5% of events passing, cause of < 2% of GEM deadtime





YETS 24-25

Year End Technical Stop (YETS) 24/25

- Status of detectors
 - GE1/1: Keep minimal HV on during the whole YETS (300 V on the foils, gaps OFF)
 - Why:
 - minimize the stress during the repowering in February 2025
 - minimize diffusion of oxide dust without HV
 - When HV OFF: during mechanical movements of CMS yokes, disruptions in power or gas system, human activity on the disk where GE1/1 is installed
 - **GE2/1**: HV OFF
 - Both GE1/1 and GE2/1 flushed in $pure\ CO_2$ during the YETS
- Installations
 - 5 new GE2/1 chambers
 - 4 chambers never contaminated by copper dust
 - 1 chamber with both PCBs and foils cleaned from copper dust
- Extractions
 - 1 GE2/1 chamber (the one with just the PCB recleaned from copper dust)
 - Few GE1/1 Super-Chambers
 - Why: to understand more on the oxidation of GE1/1 non-passivated PCBs